Dr JBO Name:

Student ID Number: Model Answer

Section:

Lecturer: Dr. Jamaludin Bin Omar

EEEB273 - Quiz 4

SEMESTER 2, ACADEMIC YEAR 2014/2015 Date: 18 December 2014 Time: 15 minutes

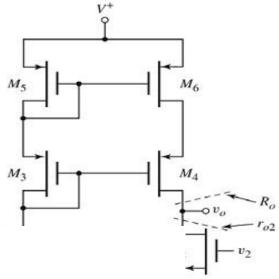
### **Question:**

For a MOSFET differential amplifier with cascode active load shown in Figure 1 the transistor parameters are  $g_m = 1.2$  mA/V for all transistors;  $K_n = 0.4$  mA/V<sup>2</sup> and  $\lambda_n = 0.020$  V<sup>-1</sup> for N-MOSFET transistors; and  $\lambda_p = 0.015$  V<sup>-1</sup> for P-MOSFET transistors.

Find bias current  $(I_0)$  and calculate one-sided differential mode gain  $(A_d)$  with output taken at  $v_0$ . Show clearly all formula used and calculations done as marks are given according to this.

[10 marks]

#### Answer:



$$g_{m} = 2 \sqrt{[K_{n2} \times I_{DQ}]}$$

$$= 2 \sqrt{[K_{n2} \times (I_{Q}/2)]}$$

$$I_{Q} = [g_{m}/2]^{2} \times [2/K_{n2}]$$

$$I_{Q} = [g_{m}/2]^{2} \times [2/K_{n2}]$$

$$= [g_{m}]^{2}/[2K_{n2}]$$

$$= [1.2m]^{2}/[2 \times 0.4m] = 1.8 \text{ mA}$$
[1]

$$= [1.2 \text{m}]^{2} / [2 \times 0.4 \text{m}] = 1.8 \text{ mA}$$
 [1]

$$I_{DQ} = I_Q / 2 = 0.9 \text{ mA}$$
 [1]

$$r_{02} = 1 / (\lambda_n I_{DQ})$$
 [1]  
= 1 / (0.020 x 0.9m) = 55.556 k $\Omega$  [1]

$$r_{04} = r_{06} = 1 / (\lambda_p I_{DQ})$$
 [1]  
= 1 / (0.015 x 0.9m) = 74.074 k $\Omega$  [1]

$$R_O = g_m r_{04} r_{06}$$
  
= (1.2m)(74.074k)(74.074k)  
= 6.584 M $\Omega$  [1]

$$A_d = g_m (r_{02} || R_0)$$
= (1.2m)(55.556k || 6.584M)
= 66.109 V/V [1]

# : N - MOSFET

$$v_{DS}(\text{sat}) = v_{GS} - V_{TN}$$

$$i_D = K_n [v_{GS} - V_{TN}]^2$$

$$K_n = \frac{k_n}{2} \cdot \frac{W}{I}$$

$$v_{SD}(\text{sat}) = v_{SG} + V_{TP}$$
$$i_D = K_p [v_{SG} + V_{TP}]^2$$
$$K_p = \frac{k_p}{2} \cdot \frac{W}{L}$$

$$g_m = 2\sqrt{K_? I_{DQ}}$$

$$r_o \cong \frac{1}{\lambda I_{DQ}}$$

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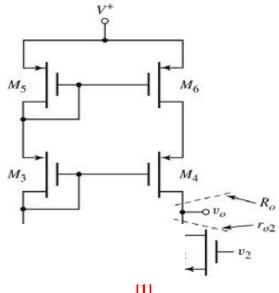
**Question:** 

For a MOSFET differential amplifier with cascode active load shown in Figure 1 the transistor parameters are  $g_m = 1.3$  mA/V for all transistors;  $K_n = 0.4$  mA/V<sup>2</sup> and  $\lambda_n = 0.015$  V<sup>-1</sup> for N-MOSFET transistors; and  $\lambda_p = 0.020$  V<sup>-1</sup> for P-MOSFET transistors.

Find bias current  $(I_0)$  and calculate one-sided differential mode gain  $(A_d)$  with output taken at  $v_0$ . Show clearly all formula used and calculations done as marks are given according to this.

[10 marks]

## Answer:



$$g_{m} = 2 \sqrt{[K_{n2} \times I_{DQ}]}$$

$$= 2 \sqrt{[K_{n2} \times (I_{Q}/2)]}$$

$$= [g_{m}/2]^{2} \times [2/K_{n2}]$$

$$I_{Q} = [g_{m}/2]^{2} \times [2/K_{n2}]$$

$$= [g_{m}]^{2}/[2 K_{n2}]$$

$$= [1.3m]^{2}/[2 \times 0.4m] = 2.113 \text{ mA}$$
[1]

$$= [1.3m]^{2} / [2 \times 0.4m] = 2.113 \text{ mA}$$

$$I_{DQ} = I_Q/2 = 1.056 \text{ mA}$$
 [1]

$$r_{02} = 1 / (\lambda_n I_{DQ})$$
 [1]  
= 1 / (0.015 x 1.056m) = 63.116 k $\Omega$  [1]

$$r_{04} = r_{06} = 1 / (\lambda_p I_{DQ})$$
 [1]  
= 1 / (0.020 x 1.056m) = 47.337 k $\Omega$  [1]

$$R_O = g_m r_{04} r_{06}$$
  
= (1.3m)(47.337k)(47.337k)  
= 2.913 M $\Omega$  [1]

$$A_d = g_m (r_{02} || R_O)$$
 [1]  
= (1.3m)(63.116k || 2.913M)  
= 80.311 V/V [1]

# : N - MOSFET

$$v_{DS}(\text{sat}) = v_{GS} - V_{TN}$$

$$i_D = K_n [v_{GS} - V_{TN}]^2$$

$$K_n = \frac{k_n'}{2} \cdot \frac{W}{L}$$

$$v_{SD}(\text{sat}) = v_{SG} + V_{TP}$$
$$i_D = K_p [v_{SG} + V_{TP}]^2$$
$$K_p = \frac{k_p}{2} \cdot \frac{W}{L}$$

$$g_m = 2\sqrt{K_? I_{DQ}}$$

$$r_o \cong \frac{1}{\lambda I_{DQ}}$$

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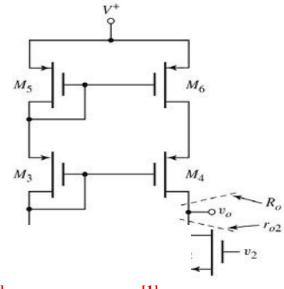
### **Question:**

For a MOSFET differential amplifier with cascode active load shown in Figure 1 the transistor parameters are  $g_m = 1.4$  mA/V for all transistors;  $K_n = 0.4$  mA/V<sup>2</sup> and  $\lambda_n = 0.020$  V<sup>-1</sup> for N-MOSFET transistors; and  $\lambda_p = 0.015$  V<sup>-1</sup> for P-MOSFET transistors.

Find bias current  $(I_Q)$  and calculate one-sided differential mode gain  $(A_d)$  with output taken at  $v_o$ . Show clearly all formula used and calculations done as marks are given according to this.

[10 marks]

#### **Answer:**



$$g_m = 2 \sqrt{[K_{n2} \times I_{DQ}]}$$
  
=  $2 \sqrt{[K_{n2} \times (I_Q/2)]}$ 

$$I_{Q} = [g_{m}/2]^{2} \times [2/K_{n2}]$$
 [1]  
=  $[g_{m}]^{2}/[2K_{n2}]$   
=  $[1.4m]^{2}/[2 \times 0.4m] = 2.450 \text{ mA}$  [1]

$$I_{DQ} = I_Q / 2 = 1.225 \text{ mA}$$
 [1]

$$r_{02} = 1 / (\lambda_n I_{DQ})$$
 [1]  
= 1 / (0.020 x 1.225m) = 40.816 k $\Omega$  [1]

$$r_{04} = r_{06} = 1 / (\lambda_p I_{DQ})$$
 [1]  
= 1 / (0.015 x 1.225m) = 54.422 k $\Omega$  [1]

$$R_O = g_m r_{04} r_{06}$$
= (1.4m)(54.422k)(54.422k)
= 4.146 M\Omega [1]

$$A_d = g_m (r_{02} || R_O)$$
 [1]  
= (1.4m)(40.816k || 4.146M)  
= 56.586 V/V [1]

# ; N – MOSFET

$$v_{DS}(\text{sat}) = v_{GS} - V_{TN}$$

$$i_D = K_n [v_{GS} - V_{TN}]^2$$

$$K_n = \frac{k_n'}{2} \cdot \frac{W}{L}$$

$$v_{SD}(\text{sat}) = v_{SG} + V_{TP}$$

$$i_D = K_p [v_{SG} + V_{TP}]^2$$

$$K_p = \frac{k_p}{2} \cdot \frac{W}{L}$$

# ;Small signal

$$g_m = 2\sqrt{K_? I_{DQ}}$$

$$r_o \cong \frac{1}{\lambda I_{DQ}}$$

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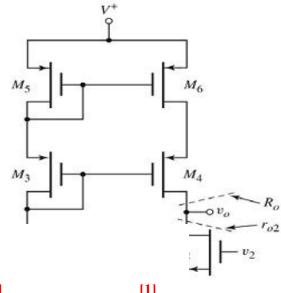
### **Question:**

For a MOSFET differential amplifier with cascode active load shown in Figure 1 the transistor parameters are  $g_m = 1.5$  mA/V for all transistors;  $K_n = 0.4$  mA/V<sup>2</sup> and  $\lambda_n = 0.015$  V<sup>-1</sup> for N-MOSFET transistors; and  $\lambda_p = 0.020$  V<sup>-1</sup> for P-MOSFET transistors.

Find bias current  $(I_Q)$  and calculate one-sided differential mode gain  $(A_d)$  with output taken at  $v_o$ . Show clearly all formula used and calculations done as marks are given according to this.

[10 marks]

#### Answer:



$$g_{m} = 2 \sqrt{[K_{n2} \times I_{DQ}]}$$

$$= 2 \sqrt{[K_{n2} \times (I_{Q}/2)]}$$

$$= [g_{m}/2]^{2} \times [2/K_{n2}]$$

$$I_Q = [g_m/2]^2 \times [2/K_{n2}]$$
 [1]  
=  $[g_m]^2/[2K_{n2}]$   
=  $[1.5m]^2/[2 \times 0.4m] = 2.813 \text{ mA}$  [1]

$$I_{DQ} = I_Q/2 = 1.406 \text{ mA}$$
 [1]

$$r_{02} = 1 / (\lambda_n I_{DQ})$$
 [1]  
= 1 / (0.015 x 1.406m) = 47.407 k $\Omega$  [1]

$$r_{04} = r_{06} = 1 / (\lambda_p I_{DQ})$$
 [1]  
= 1 / (0.020 x 1.406m) = 35.556 k $\Omega$  [1]

$$R_O = g_m r_{04} r_{06}$$
  
= (1.5m)(35.556k)(35.556k)  
= 1.896 M $\Omega$  [1]

$$A_d = g_m (r_{o2} || R_O)$$
 [1]  
= (1.5m)(47.407k || 1.896M)  
= 69.377 V/V [1]

# ; N – MOSFET

$$v_{DS}(\text{sat}) = v_{GS} - V_{TN}$$

$$i_D = K_n [v_{GS} - V_{TN}]^2$$

$$K_n = \frac{k_n'}{2} \cdot \frac{W}{L}$$

$$v_{SD}(\text{sat}) = v_{SG} + V_{TP}$$
$$i_D = K_p [v_{SG} + V_{TP}]^2$$
$$K_p = \frac{k_p}{2} \cdot \frac{W}{L}$$

$$g_m = 2\sqrt{K_? I_{DQ}}$$

$$r_o \cong \frac{1}{\lambda I_{DQ}}$$